

Silicon NPN Power Transistors

2SD798

DESCRIPTION

- With TO-220 package
- High voltage
- DARLINGTON

APPLICATIONS

- With switching and igniter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

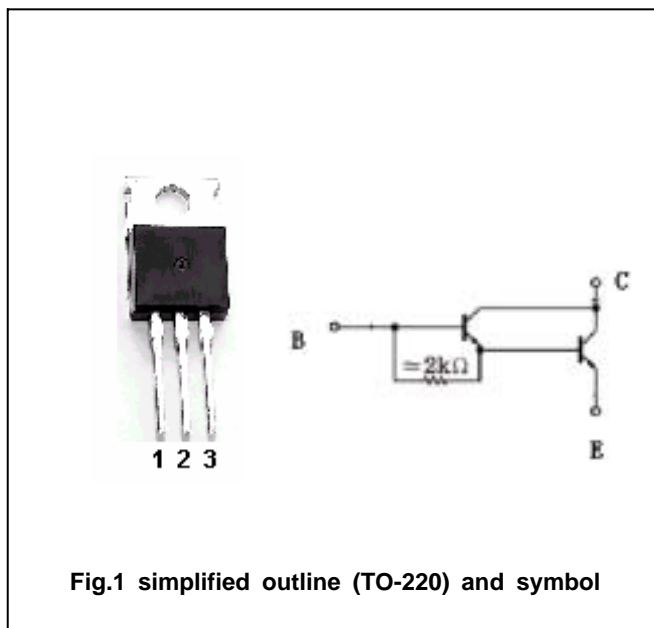


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	600	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	300	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		6	A
I <sub>B</sub>	Base current		1	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	30	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.5A ; L=40mH	300			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.04A			2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.04A			2.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =600V; I <sub>E</sub> =0			0.5	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.5	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =2V	1500			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =4A ; V <sub>CE</sub> =2V	200			
C <sub>OB</sub>	Collector output capacitance	f=1MHz; V <sub>CB</sub> =50V		35		pF

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>B1</sub> =-I <sub>B2</sub> =0.04A V <sub>CC</sub> 100V, R <sub>L</sub> =25		1		μs
t <sub>stg</sub>	Storage time			8		μs
t <sub>f</sub>	Fall time			5		μs

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PACKAGE OUTLINE

